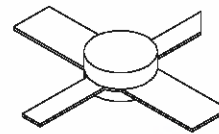




MSC1004MP

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- 1025 - 1150 MHz
- RUGGEDIZED VSWR $\infty:1$
- INTERNAL INPUT MATCHING
- LOW THERMAL RESISTANCE
- $P_{OUT} = 4.0 \text{ W MIN. WITH } 9.0 \text{ dB GAIN}$



.280 4LFL (SO51)
epoxy sealed

ORDER CODE
MSC1004MP

BRANDING
1004MP

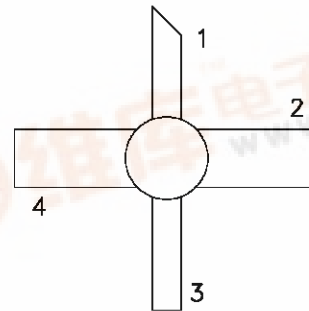
DESCRIPTION

The MSC1004MP is a low-level Class C pulsed transistor specifically designed for DME/IFF driver or output applications.

These devices are capable of withstanding a $\infty:1$ load VSWR at any phase angle under full rated conditions. Low RF thermal resistance and automatic bonding techniques ensure high reliability and product consistency.

The MSC1004MP is housed in the IMPAC™ package with internal input matching.

PIN CONNECTION



1. Collector 3. Emitter
2. Base 4. Base

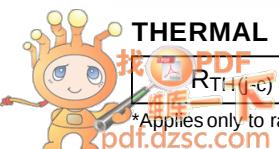
ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation* ($T_C \leq 100^{\circ}\text{C}$)	18	W
I_C	Device Current*	650	mA
V_{CC}	Collector-Supply Voltage*	32	V
T_J	Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(J-C)}$	Junction-Case Thermal Resistance*	5	$^{\circ}\text{C/W}$
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*Applies only to rated RF amplifier operation



ELECTRICAL SPECIFICATIONS ($T_{case} = 25^{\circ}C$)

STATIC

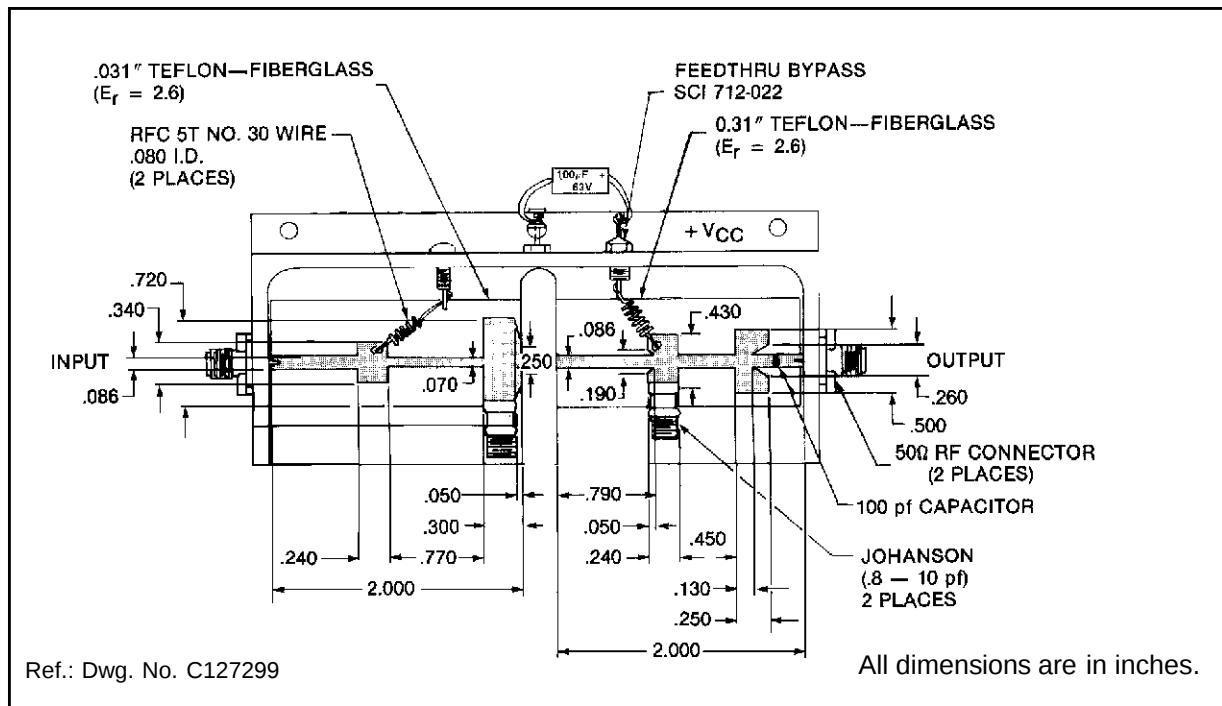
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	$I_C = 1 \text{ mA}$ $I_E = 0 \text{ mA}$	45	—	—	V
BV_{CER}	$I_C = 5 \text{ mA}$ $R_{BE} = 10 \Omega$	45	—	—	V
BV_{EBO}	$I_E = 1 \text{ mA}$ $I_C = 0 \text{ mA}$	3.5	—	—	V
I_{CES}	$V_{CE} = 28 \text{ V}$	—	—	1.0	mA
h_{FE}	$V_{CE} = 5 \text{ V}$ $I_C = 200 \text{ mA}$	30	—	300	—

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	$f = 1025 - 1150 \text{ MHz}$ $P_{IN} = 500 \text{ mW}$ $V_{CC} = 28 \text{ V}$	4.0	—	—	W
η_C	$f = 1025 - 1150 \text{ MHz}$ $P_{IN} = 500 \text{ mW}$ $V_{CC} = 28 \text{ V}$	35	—	—	%
G_P	$f = 1025 - 1150 \text{ MHz}$ $P_{IN} = 500 \text{ mW}$ $V_{CC} = 28 \text{ V}$	9.0	—	—	dB

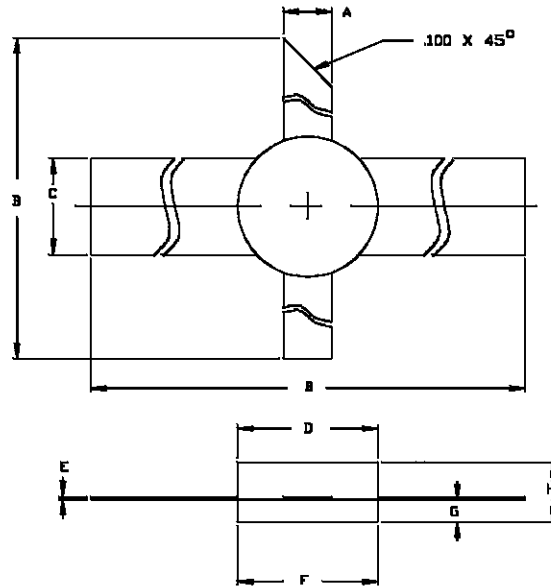
Note: Pulse Width = $10\mu\text{Sec}$
Duty Cycle = 1%

TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0217 rev. A



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.095/2,41	.105/2,67
B	1.050/26,67	
C	.195/4,95	.205/5,21
D	.275/6,99	.285/7,24
E	.004/0,10	.007/0,18
F		.280/7,11
G	.050/1,27	.070/1,78
H		.145/3,68

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